

MC74VHCT125A

Quad Bus Buffer

with 3-State Control Inputs

The MC74VHCT125A is a high speed CMOS quad bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHCT125A requires the 3-state control input (\overline{OE}) to be set High to place the output into the high impedance state.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT125A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

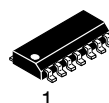
- High Speed: $t_{PD} = 3.8$ ns (Typ) at $V_{CC} = 5.0$ V
- Low Power Dissipation: $I_{CC} = 4.0$ μ A (Max) at $T_A = 25^\circ$ C
- TTL-Compatible Inputs: $V_{IL} = 0.8$ V; $V_{IH} = 2.0$ V
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8$ V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
 - Human Body Model > 2000 V;
 - Machine Model > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



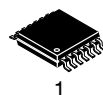
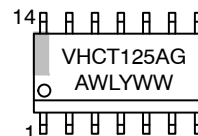
ON Semiconductor®

www.onsemi.com

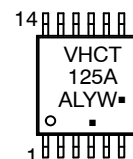
MARKING DIAGRAMS



SOIC-14
D SUFFIX
CASE 751A



TSSOP-14
DT SUFFIX
CASE 948G



A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
WW, W = Work Week
G or ■ = Pb-Free Package

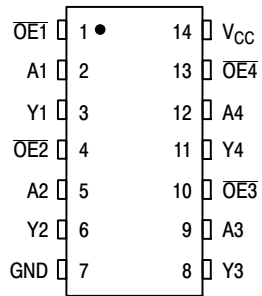
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MC74VHCT125A

PIN CONNECTION (Top View)

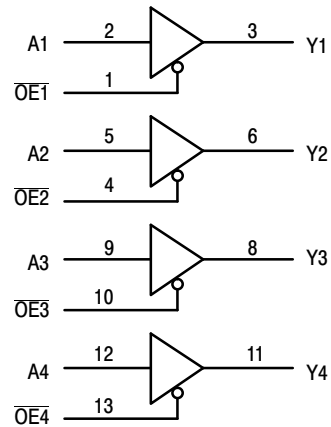


FUNCTION TABLE

VHCT125A		
Inputs		Output
A	OE	Y
H	L	H
L	L	L
X	H	Z

LOGIC DIAGRAM

Active-Low Output Enables



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT125ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT125ADTRG	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLVVHCT125ADTRG*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

MC74VHCT125A

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage Output in 3-State High or Low State	-0.5 to +7.0 -0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current (V _{OUT} < GND; V _{OUT} > V _{CC})	±20	mA
I _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage Output in 3-State High or Low State	0 0	5.5 V _{CC}	V
T _A	Operating Temperature	-55	+125	°C
t _r , t _f	Input Rise and Fall Time V _{CC} = 5.0 V ± 0.5 V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} (V)	T _A = 25°C			T _A ≤ 85°C		T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		3.0	1.2			1.2		1.2		V
			4.5	2.0		2.0		2.0			
			5.5	2.0		2.0		2.0			
V _{IL}	Maximum Low-Level Input Voltage		3.0			0.53		0.53		0.53	V
			4.5			0.8		0.8		0.8	
			5.5			0.8		0.8		0.8	
V _{OH}	Minimum High-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OH} = -50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
		V _{IN} = V _{IH} or V _{IL} I _{OH} = -4.0 mA I _{OH} = -8.0 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage V _{IN} = V _{IH} or V _{IL}	V _{IN} = V _{IH} or V _{IL} I _{OL} = 50 μA	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
		V _{IN} = V _{IH} or V _{IL} I _{OL} = 4.0 mA I _{OL} = 8.0 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±0.1		±0.1	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			2.0		20		40	μA
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OZ}	Maximum Three-State Leakage Current	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND	5.5			±0.25		±2.5		±2.5	μA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μA

MC74VHCT125A

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions	$T_A = 25^\circ\text{C}$			$T_A = \leq 85^\circ\text{C}$		$T_A \leq 125^\circ\text{C}$		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PLH} , t_{PHL}	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 15$ pF $C_L = 50$ pF		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 15$ pF $C_L = 50$ pF		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
t_{PZL} , t_{PZH}	Maximum Output Enable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 15$ pF $R_L = 1.0$ k Ω $C_L = 50$ pF		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 15$ pF $R_L = 1.0$ k Ω $C_L = 50$ pF		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t_{PLZ} , t_{PHZ}	Maximum Output Disable Time, $\overline{\text{OE}}$ to Y	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 50$ pF $R_L = 1.0$ k Ω		9.5	13.2	1.0	15.0		18.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 50$ pF $R_L = 1.0$ k Ω		6.1	8.8	1.0	10.0		12.0	
t_{OSLH} , t_{OSHL}	Output-to-Output Skew	$V_{CC} = 3.3 \pm 0.3$ V $C_L = 50$ pF (Note 1)			1.5		1.5		2.0	ns
		$V_{CC} = 5.0 \pm 0.5$ V $C_L = 50$ pF (Note 1)			1.0		1.0		1.5	
C_{in}	Maximum Input Capacitance			4	10		10		10	pF
C_{out}	Maximum Three-State Output Capacitance (Output in High Impedance State)			6						pF

C_{PD}	Power Dissipation Capacitance (Note 2)	Typical @ 25°C , $V_{CC} = 5.0\text{V}$				pF
		14				

- Parameter guaranteed by design. $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$.
- C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/4$ (per buffer). C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

Symbol	Characteristic	$T_A = 25^\circ\text{C}$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	- 0.3	- 0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

MC74VHCT125A

SWITCHING WAVEFORMS

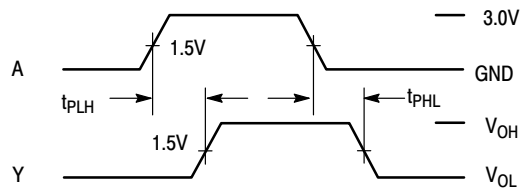


Figure 1.

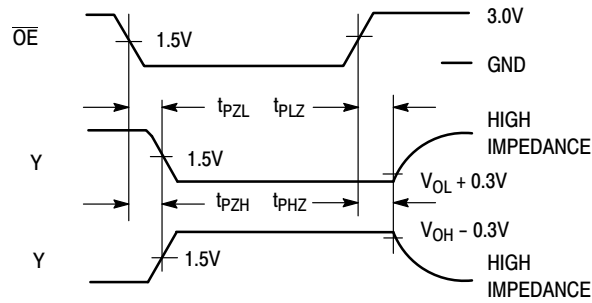
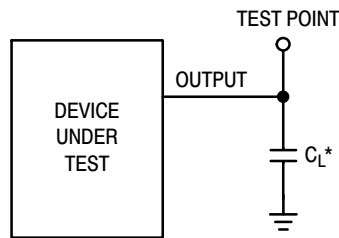
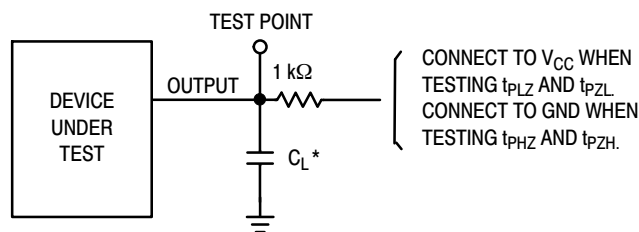


Figure 2.



*Includes all probe and jig capacitance

Figure 3. Test Circuit



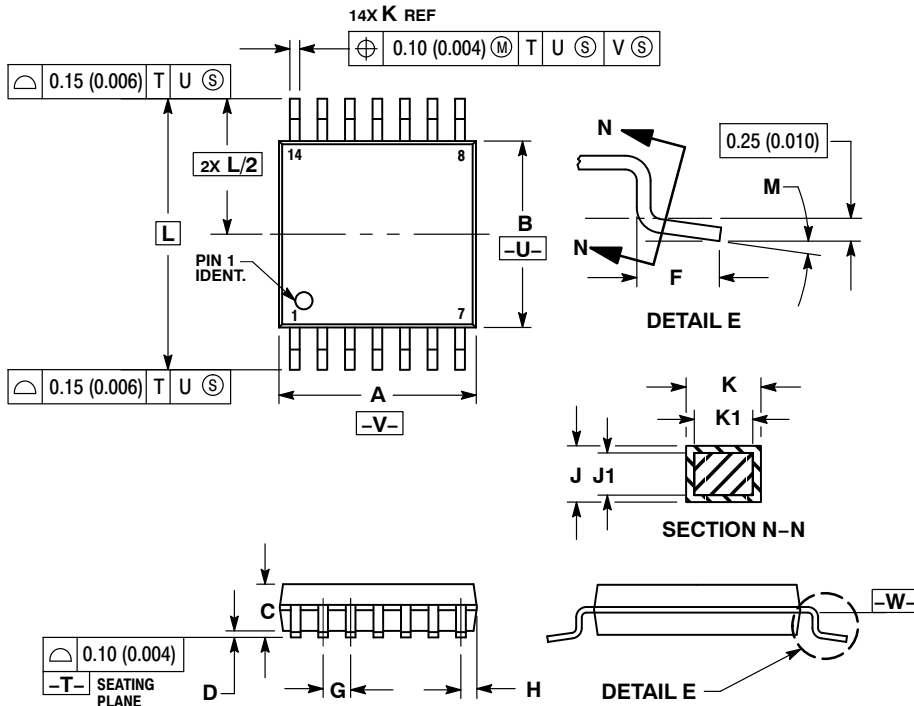
*Includes all probe and jig capacitance

Figure 4. Test Circuit

MC74VHCT125A

PACKAGE DIMENSIONS

TSSOP-14
DT SUFFIX
CASE 948G
ISSUE B

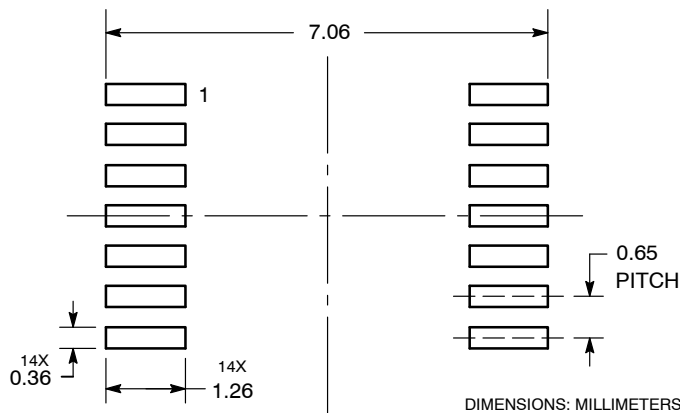


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT



ON Semiconductor and the are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative